

Mono N-Type Silicon Wafer(G12)

210X210



Geometric Parameter

Side length	210±0.25mm
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Diagonal	295±0.25mm
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Thickness	130(+10/-8)μm
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Arc length projection	1.41±0.5mm
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Electrical Properties

Resistivity	0.6-1.6Ω·cm
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Minority carrier	≥1000μs
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Oxygen content	≤5.75×10 ¹⁷ at/cm ³
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Carbon content	≤5×10 ¹⁶ at/cm ³
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Material Properties

Growth method	CZ
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Orientation	<100>±2°
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Surface Performance

TTV	≤20
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Warpage	≤40
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Line mark	≤13
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Edge collapse	Depth≤0.3mm, length≤0.5mm, no more than one places
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Cracks and perforations	Invisible by visual inspection
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Silicon wafer surface	Clean, free of oil, soap, glue and other residues
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